



WBFBP-03B Plastic-Encapsulate Transistors

MMBT3904M TRANSISTOR

DESCRIPTION

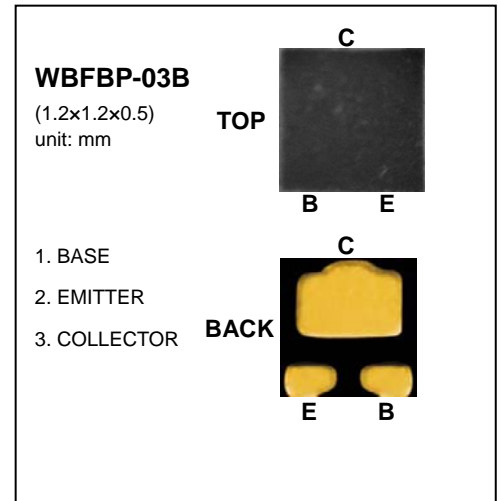
NPN Epitaxial Silicon Transistor

FEATURES

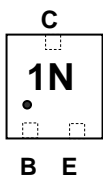
- Epitaxial Planar Die Construction
- Complementary PNP Type Available (MMBT3906M)
- Ultra-Small Surface Mount Package
- Also Available in Lead Free Version

APPLICATION

General Purpose Amplifier, switching
 For portable equipment:(i.e. Mobile phone,MP3, MD,CD-ROM, DVD-ROM, Note book PC, etc.)



MARKING:1N



MAXIMUM RATINGS* $T_A=25^{\circ}\text{C}$ unless otherwise noted

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	60	V
V_{CEO}	Collector-Emitter Voltage	40	V
V_{EBO}	Emitter-Base Voltage	6	V
I_C	Collector Current -Continuous	0.2	A
P_C	Collector Dissipation	0.15	W
T_J	Junction Temperature	150	$^{\circ}\text{C}$
T_{stg}	Storage Temperature	-55-150	$^{\circ}\text{C}$

ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=10\mu\text{A}, I_E=0$	60			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=1\text{mA}, I_B=0$	40			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=10\mu\text{A}, I_C=0$	6			V
Collector cut-off current	I_{CEX}	$V_{CE}=30\text{V}, V_{EB(off)}=3\text{V}$			0.05	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=5\text{V}, I_C=0$			0.1	μA
DC current gain	$h_{FE(1)}$	$V_{CE}=1\text{V}, I_C=0.1\text{mA}$	40			
	$h_{FE(2)}$	$V_{CE}=1\text{V}, I_C=1\text{mA}$	70			
	$h_{FE(3)}$	$V_{CE}=1\text{V}, I_C=10\text{mA}$	100		300	
	$h_{FE(4)}$	$V_{CE}=1\text{V}, I_C=50\text{mA}$	60			
	$h_{FE(5)}$	$V_{CE}=1\text{V}, I_C=100\text{mA}$	30			
Collector-emitter saturation voltage	$V_{CE(sat)1}$	$I_C=10\text{mA}, I_B=1\text{mA}$			0.2	V
	$V_{CE(sat)2}$	$I_C=50\text{mA}, I_B=5\text{mA}$			0.3	V
Base-emitter saturation voltage	$V_{BE(sat)1}$	$I_C=10\text{mA}, I_B=1\text{mA}$	0.65		0.85	V
	$V_{BE(sat)2}$	$I_C=50\text{mA}, I_B=5\text{mA}$			0.95	V
Transition frequency	f_T	$V_{CE}=20\text{V}, I_C=10\text{mA}, f=100\text{MHz}$	300			MHz

ELECTRICAL CHARACTERISTICS (Tamb=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector output capacitance	C _{ob}	V _{CB} =5V, I _E =0, f=1MHz			4	pF
Noise figure	NF	V _{CE} =5V, I _c =0.1mA,			5	dB
Delay time	t _d	V _{CC} =3V, V _{BE (off)} = -0.5V, I _C =10mA, I _{B1} =1mA			35	nS
Rise time	t _r				35	nS
Storage time	t _S	V _{CC} =3V, I _C =10mA			200	nS
Fall time	t _f	I _{B1} = I _{B2} = 1mA			50	nS

Typical Characteristics

MMBT3904M

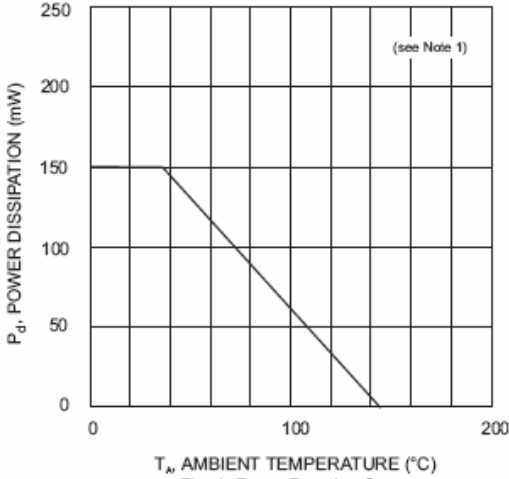


Fig. 1, Power Derating Curve

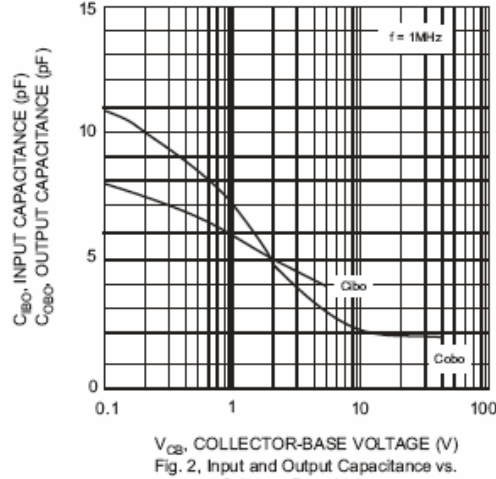


Fig. 2, Input and Output Capacitance vs. Collector-Base Voltage

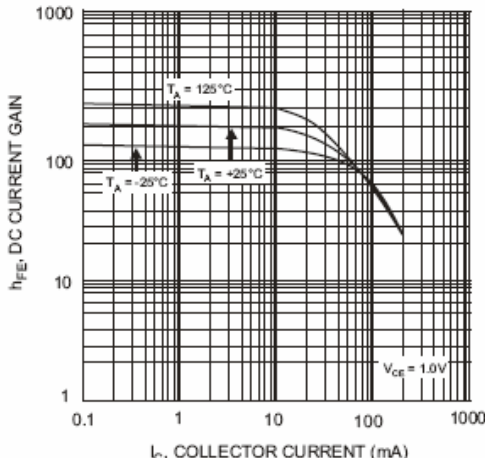


Fig. 3, Typical DC Current Gain vs. Collector Current

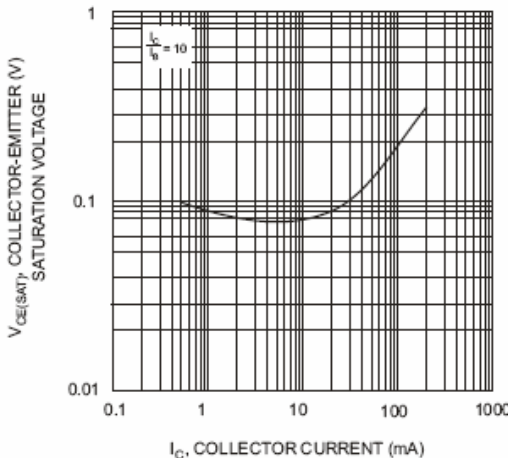


Fig. 4, Typical Collector-Emitter Saturation Voltage vs. Collector Current

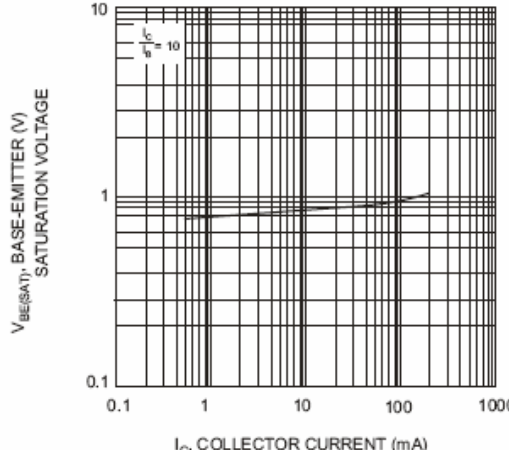
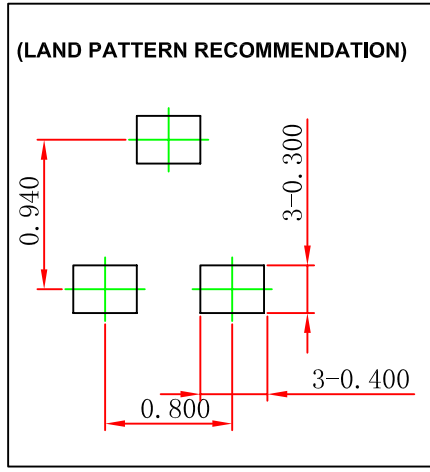
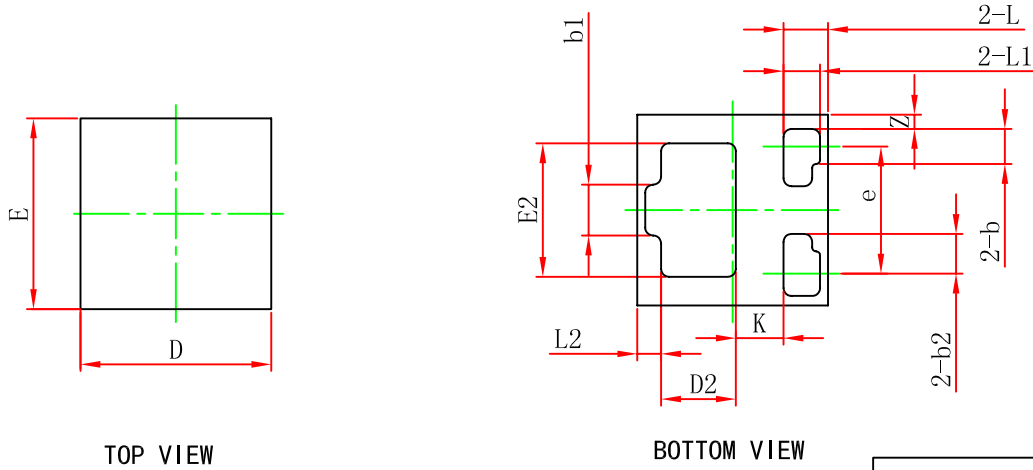


Fig. 5, Typical Base-Emitter Saturation Voltage vs. Collector Current

WBFBP-03B(1.2×1.2×0.5) PACKAGE OUTLINE DIMENSIONS



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.450	0.550	0.018	0.022
A1	0.010	0.090	0.000	0.004
b	0.170	0.270	0.007	0.011
b1	0.270	0.370	0.011	0.015
b2	0.250 REF.		0.010 REF.	
D	1.150	1.250	0.045	0.049
E	1.150	1.250	0.045	0.049
D2	0.470 REF.		0.002 REF.	
E2	0.810 REF.		0.032 REF.	
e	0.800 TYP.		0.032 TYP.	
L	0.280 REF.		0.011 REF.	
L1	0.230 REF.		0.009 REF.	
L2	0.150 REF.		0.006 REF.	
k	0.300 REF.		0.012 REF.	
z	0.090 REF.		0.004 REF.	